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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Katsuhiko Fukasaku

Serial No.: 10/050,165

Group Art Unit: 2811

Filed: January 18, 2002

Examiner: Im, Junghwa

For: SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME

Honorable Commissioner of Patents  
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated **September 24, 2002**, please amend the above-identified application as follows:

IN THE CLAIMS:

**Please cancel claims 4-6 without prejudice or disclaimer.**

**Please amend the following claims:**

1. (Amended) A semiconductor device comprising:

a plurality of transistors comprising different gate insulator film in their thickness value, said plurality of transistors having different thickness values of a gate electrode thereof in correspondence to the thickness values of the gate insulator film thereof,

wherein said plurality of transistors comprise a first lightly doped drain region, and

wherein said gate electrode includes an impurity to suppress depletion when forming a source region and a drain region, and one of said source region and said drain region is thinner than the other region.

→ Not in the spec  
in the figures...

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